

IN THE CLAIMS

Please amend the claims as follows:

1-3. (Canceled)

4. (Currently amended) ~~The semiconductor device of claim 2,~~ A semiconductor device comprising:

an internal voltage supply circuit for generating an internal voltage from a power supply voltage;

an internal circuit which is operated by the internal voltage;

a switching transistor for receiving at a gate an operation signal output from the internal circuit; and

a load circuit which is connected to a drain of the switching transistor and consumes substantially the same amount of electric current as the amount of electric current which the internal circuit consumes during an operation period,

wherein by the operation signal, the switch transistor is turned OFF when the internal circuit is in an operation state and is turned ON when the internal circuit is in a non-operation state, and

the load circuit includes a first resistor and a load adjustment section connected in series to the first resistor.

5. (Currently amended) The semiconductor device of claim 4, wherein the amount of electric current which the first resistor and the load adjustment section consume is ~~the~~ substantially the same as the amount of electric current which the internal circuit consumes during an operation period.

6. (Original) The semiconductor device of claim 5, wherein the load adjustment section

includes a second resistor and a fuse device connected in parallel to each other.

7. (Original) The semiconductor device of claim 5, wherein the load adjustment section includes a second resistor and a transistor connected in parallel to each other.

8. (Original) The semiconductor device of claim 7, further comprising a latch circuit connected to the transistor.

9. (Currently amended) The semiconductor device of claim 4 ~~[[1]]~~, wherein the switching switch transistor is an n-channel transistor.

10. (Original) The semiconductor device of claim 9, wherein the switching transistor has a source grounded and a drain connected to the internal voltage supply circuit via the load circuit.

11. (Currently amended) The semiconductor device of claim 4 ~~[[1]]~~, wherein the switching switch transistor is a p-channel transistor.

12. (Currently amended) The semiconductor device of claim 11, wherein the switching switch transistor has a source connected to the internal voltage supply circuit and a drain grounded via the load circuit.

13. (Currently amended) An IC card comprising:
a semiconductor device which includes an internal voltage supply circuit for generating an internal voltage from a power supply voltage,
an internal circuit which is operated by the internal voltage,
a switching transistor for receiving at a gate an operation signal output from the internal circuit, and
a load circuit which is connected to a drain of the switching transistor and consumes substantially the same amount of electric current as the amount of electric current which the

internal circuit consumes during an operation period and in which by the operation signal, the switching switch transistor is turned OFF when the internal circuit is in an operation state and is turned ON when the internal circuit is in a non-operation state,

wherein the load circuit includes a first resistor and a load adjustment section connected in series to the first resistor.

14. (New) A semiconductor device comprising:

an internal voltage supply circuit for generating an internal voltage from a power supply voltage;

an internal circuit which is operated by the internal voltage;

a switching transistor for receiving at a gate an operation signal output from the internal circuit; and

a load circuit which is connected to a drain of the switching transistor and consumes substantially the same amount of electric current as the amount of electric current which the internal circuit consumes during an operation period,

wherein by the operation signal, the switching transistor is turned OFF when the internal circuit is in an operation state and is turned ON when the internal circuit is in a non-operation state, and

the load circuit includes a load adjustment section for adjusting the amount of electric current which the load circuit consumes.

15. (New) The semiconductor device of claim 14, wherein the load adjustment section includes a second resistor and a fuse device which are connected in parallel to each other,

the amount of electric current which the first resistor consumes is more than the amount of electric current which the internal circuit consumes during an operation period when the fuse device is not cut, and

the amount of electric current which the load circuit consumes is substantially the same as the amount of electric current which the internal circuit consumes when the fuse device is cut.